TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VHCT245AF,TC74VHCT245AFT,TC74VHCT245AFK

Octal Bus Transceiver

The TC74VHCT245A is an advanced high speed CMOS OCTAL BUS TRANSCEIVER fabricated with silicon gate C²MOS technology. It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

It is intended for two-way asynchronous communication between data busses. The direction of data transmission is determined by the level of the DIR input.

The enable input ($\overline{\rm G}$) can be used to disable the device so that the busses are effectively isolated.

The input voltage are compatible with TTL output voltage.

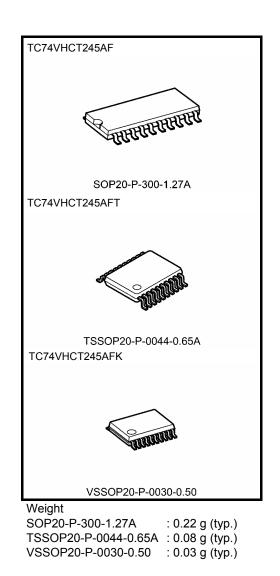
This device may be used as a level converter for interfacing 3.3 V to 5 V system.

Input protection and output circuit ensure that 0 to 5.5 V can be applied to the input and output ^(Note) pins without regard to the supply voltage. These structure prevents device destruction due to mismatched supply and input/output voltages such as battery back up, hot board insertion, etc.

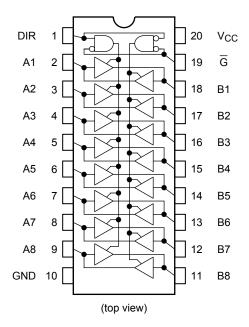
Note: Output in off-state

Features (Note)

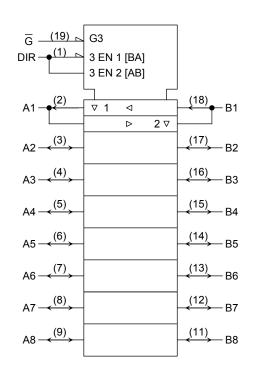
- High speed: $t_{pd} = 4.9$ ns (typ.) at $V_{CC} = 5$ V
- Low power dissipation: $I_{CC} = 4 \mu A (max)$ at $Ta = 25^{\circ}C$
- Compatible with TTL outputs: $V_{IL} = 0.8 V (max)$
 - $V_{IH} = 2.0 V (min)$
- Power down protection is provided on all inputs and outputs
- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Low noise: V_{OLP} = 1.6 V (max)
- Pin and function compatible with the 74 series (74AC/HC/F/ALS/LS etc.) 245 type.
 - Note: Do not apply a signal to any bus terminal when it is in the output mode. Damage may result.
 All floating (high impedance) bus terminals must have their input levels fixed by means of pull up or pull down resistors.



Pin Assignment



IEC Logic Symbol



Truth Table

ĺ	Inp	uts	Fund	Output			
	Ğ	DIR	A Bus	B Bus	Output		
	L	L	Output	Input	A = B		
	L	Н	Input	Output	B = A		
	Н	Х	2	Z			

X: Don't care

Z: High impedance

Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5 to 7.0	V
DC input voltage (DIR, \overline{G})	V _{IN}	-0.5 to 7.0	V
DC bus I/O voltage	Mue	-0.5 to 7.0 (Note 2)	V
DC bus I/O voltage	V _{I/O}	-0.5 to V _{CC} + 0.5 (Note 3)	v
Input diode current	l _{IK}	-20	mA
Output diode current	I _{ОК}	±20 (Note 4)	mA
DC output current	IOUT	±25	mA
DC V _{CC} /ground current	ICC	±75	mA
Power dissipation	PD	180	mW
Storage temperature	T _{stg}	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 2: Output in off-state
- Note 3: High or low state. IOUT absolute maximum rating must be observed.

Note 4: V_{OUT} < GND, V_{OUT} > V_{CC}

Operating Ranges (Note 1)

Characteristics	Symbol	Unit	
Supply voltage	V _{CC}	4.5 to 5.5	V
Input voltage (DIR, G)	V _{IN}	0 to 5.5	V
Bus I/O voltage	Mue	0 to 5.5 (Note 2)	V
Bus I/O Voltage	V _{I/O}	0 to V _{CC} (Note 3)	v
Operating temperature	T _{opr}	-40 to 85	°C
Input rise and fall time	dt/dV	0 to 20	ns/V

Note 1: The operating ranges are required to ensure the normal operation of the device. Unused inputs and bus inputs must be tied to either VCC or GND. Please connect both bus inputs and the bus outputs with VCC or GND when the I/O of the bus terminal changes by the function. In this case, please note that the output is not short-circuited.

Note 2: Output in off-state

Note 3: High or low state

Electrical Characteristics

DC Characteristics

Characteristics	Symbol	Test Condition		Ta = 25°C			Ta = -40 to 85°C		Unit	
	-,			$V_{CC}(V)$	Min	Тур.	Max	Min	Max	
High-level input voltage	V _{IH}	—		4.5 to 5.5	2.0	_	_	2.0	_	V
Low-level input voltage	V _{IL}	_		4.5 to 5.5		_	0.8		0.8	V
High-level output	Mari	VIN	I _{OH} = -50 μA	4.5	4.4	4.5	_	4.4		v
voltage	V _{OH}	= V _{IH} or V _{IL}	I _{OH} = -8 mA	4.5	3.94	—	—	3.80		
Low-level output	V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 50 μA	4.5	_	0.0	0.1	_	0.1	· V
voltage			I _{OL} = 8 mA	4.5	_	_	0.36	_	0.44	
3-state output off-state current	I _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or } GND$		5.5	_	_	±0.25	_	±2.50	μΑ
Input leakage current	I _{IN}	V _{IN} = 5.5 V or GND		0 to 5.5		_	±0.1	_	±1.0	μA
	ICC	V _{IN} = V _{CC} or GND		5.5	_	_	4.0	_	40.0	μA
Quiescent supply current	Ісст	Per input: V _{IN} = 3.4 V Other input: V _{CC} or GND		5.5	_	_	1.35	_	1.50	mA
Output leakage current	I _{OPD}	V _{OUT} = 5.5 V		0		_	0.5		5.0	μA

AC Characteristics (input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition		Ta = 25°C			Ta = -40 to 85°C		Unit	
	,		$V_{CC}(V)$	C _L (pF)	Min	Тур.	Max	Min	Max	
Propagation delay	t _{pLH}		5.0 ± 0.5	15		4.9	7.7	1.0	8.5	ns
time	t _{pHL}			50	_	5.4	8.7	1.0	9.5	
3-state output enable	t _{pZL}		5.0 ± 0.5	15	_	9.4	13.8	1.0	15.0	
time	t _{pZH}	$R_L = 1 k\Omega$		50	_	9.9	14.8	1.0	16.0	ns
3-state output disable	t _{pLZ}	$R_L = 1 \ k\Omega$	5.0 ± 0.5	50		10.1	15.4	1.0	16.5	ns
time	t _{pHZ}									115
Output to output skew	t _{osLH}	(Note 1)	5.0 ± 0.5	50		_	1.0		1.0	ns
Supur to Supur skew	t _{osHL}	, , , , , , , , , , , , , , , , , , ,	0.0 ± 0.0	00			1.0		1.0	110
Input capacitance	CIN	DIR, G			—	4	10	_	10	pF
Bus input capacitance	C _{I/O}	An, Bn				13	_		_	pF
Power dissipation capacitance	C _{PD}			(Note 2)		16				pF

Note 1: Parameter guaranteed by design.

 $t_{\text{OSLH}} = |t_{\text{pLHm}} - t_{\text{pLHn}}|, \ t_{\text{OSHL}} = |t_{\text{pHLm}} - t_{\text{pHLn}}|$

Note 2: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$ (per bit)

Noise Characteristics (input: $t_r = t_f = 3 \text{ ns}$)

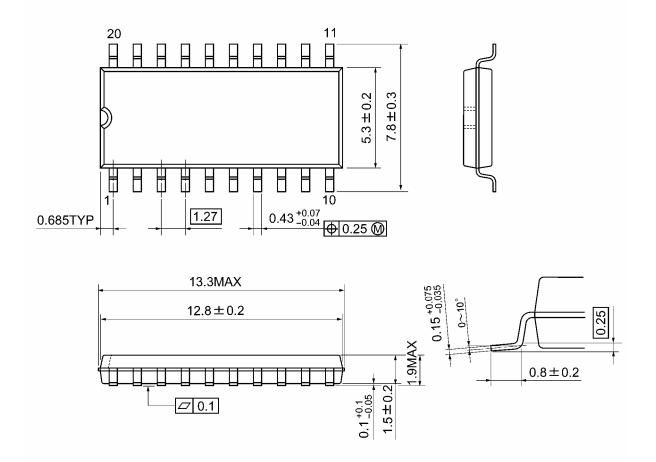
Characteristics	Symbol	Test Condition	Ta =		25°C	Unit
Characteristics	Symbol		V _{CC} (V)	Тур.	Limit	Unit
Quiet output maximum dynamic V_{OL}	V _{OLP}	C _L = 50 pF	5.0	1.1	1.5	V
Quiet output minimum dynamic V_{OL}	V _{OLV}	C _L = 50 pF	5.0	-1.1	-1.5	V
Minimum high level dynamic input voltage	V _{IHD}	C _L = 50 pF	5.0	_	2.0	V
Maximum low level dynamic input voltage	V _{ILD}	C _L = 50 pF	5.0	_	0.8	V



Package Dimensions

SOP20-P-300-1.27A

Unit: mm



Weight: 0.22 g (typ.)

Unit: mm

Package Dimensions

TSSOP20-P-0044-0.65A

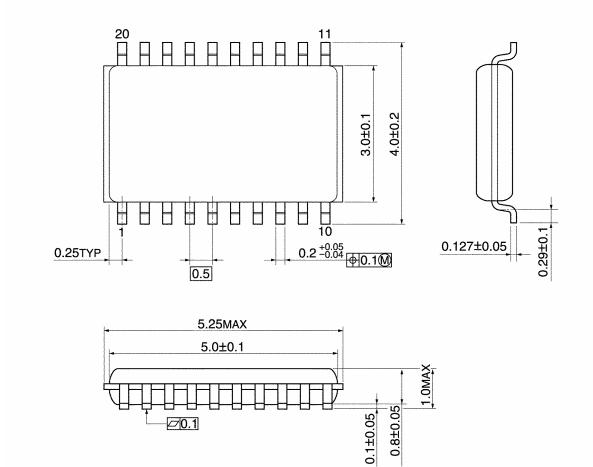
20 П 11 || 6.4±0.2 **4.4±0.1** ₿ 10 Ħ Ħ Ħ Ħ Ħ Ħ Ħ Ţ Π $0.22\substack{+0.09\\-0.06}$ 0.65 0.325TYP ∲0.13∭ 6.9MAX 6.5±0.1 1.2MAX ╔<u></u>┲р┙ 0.15+0.03 * 0~10° 0.25 1.0±0.05 0.1±0.05 S ∠70.1S (0.5) 0.45~0.75

Weight: 0.08 g (typ.)

Package Dimensions

VSSOP20-P-0030-0.50

Unit: mm



Weight: 0.03 g (typ.)

RESTRICTIONS ON PRODUCT USE

20070701-EN

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